



Attorney's Docket No. 42390P10606

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Qing Ma, Peng Cheng

Serial No. 09/894,334

Filed: June 27, 2001

For: SACRIFICIAL LAYER TECHNIQUE
TO MAKE GAPS IN MEMS
APPLICATIONS

Examiner: Coleman, William D.

Art Unit: 2823

Confirmation No.: 6477

#3 / Change
11/25/02
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TECHNOLOGY CENTER 2800

AMENDMENT AND RESPONSE TO OFFICE ACTION

Box Amendments - No Fee.
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the above-referenced application as follows, and consider the following remarks.

IN THE SPECIFICATION

On page 10, please amend paragraph 54 as follows:

It is appreciated that in addition to the horizontal and vertical gaps defined by the thickness of sacrificial material 230, additional gaps can similarly be formed in the structure defined, for example, by conventional lithographic techniques. **Figure 9** shows the structure of **Figure 7**, according to an alternative embodiment of this example, where gap 280 is patterned in the structure by, for example, photolithographic and etch techniques known in the art. **Figure 10** shows the structure of **Figure 9** after the removal of sacrificial material 230. The resulting structure includes vertical gaps 250A and 250B and horizontal gaps 260A, 260B, and 260C defined by the thickness of sacrificial material 230 (vertical gap width, horizontal gap height). **Figure 10** also shows structure with a wider gap 280 formed by photolithographic means.